

Type Designator: 2SB135

Material of Transistor: Ge

Polarity: PNP

Maximum Collector Power Dissipation (P_c): 0.1 W

Maximum Collector-Base Voltage $|V_{cb}|$: 30 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 30 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 15 V

Maximum Collector Current $|I_c \text{ max}|$: 0.1 A

Max. Operating Junction Temperature (T_j): 85 °C

Transition Frequency (f_t): 0.3 MHz

Forward Current Transfer Ratio (h_{FE}), MIN: 70

Noise Figure, dB: -

Package: TO1